

Contents

Part I Concepts

1 The History of Heterostructure Lasers	
Zhores I. Alferov	3
1.1 Introduction	3
1.2 The DHS Concept and Its Application for Semiconductor Lasers ..	3
1.3 Quantum Dot Heterostructure Lasers	12
1.4 Future Trends	18
References	19
2 Stress-Engineered Quantum Dots: Nature's Way	
Anupam Madhukar	23
2.1 Introduction	23
2.2 Corrugated Surface Stress and Lattice-Matched Growth: Surface Mechano-Chemistry	25
2.3 Lattice-Mismatch Stress and Growth Front Morphology Evolution	29
2.4 Island Induced Stress Evolution in Capping Layers	47
2.5 Stress-Driven Vertically Self-Organized Growth	51
2.6 Stress-Directed Spatially Selective Quantum Dot Arrays	54
2.7 Conclusion	59
References	60

Part II Physics

3 Characterization of Structure and Composition of Quantum Dots by Transmission Electron Microscopy	
Kurt Scheerschmidt, Peter Werner	67
3.1 Introduction	67
3.2 TEM Investigations of Quantum Dots	70
3.3 Structure Investigations of Quantum Dots	84
3.4 Conclusion and Outlook	92
References	94

VIII Contents

**4 Scanning Tunneling Microscopy Characterization
of InAs Nanostructures Formed on GaAs(001)**

Shigehiko Hasegawa, Hisao Nakashima	99
4.1 Introduction	99
4.2 Experimental Technique	100
4.3 InAs Growth on GaAs(001) by MBE	102
4.4 Post-Growth Annealing Effect on InAs Nanostructures	112
4.5 Summary	115
References	115

**5 Cross-sectional Scanning Tunneling Microscopy
at InAs Quantum Dots**

Mario Dähne, Holger Eisele	117
5.1 Introduction	117
5.2 Contrast Mechanisms in XSTM Experiments	119
5.3 Methods	121
5.4 Results	122
5.5 Discussion	129
5.6 Summary and Outlook	131
References	132

6 X-ray Characterization of Group III-Nitrides (Al,In,Ga)N

Alois Krost	135
6.1 Introduction	135
6.2 Crystal Structure and Mosaicity	135
6.3 High-Resolution X-ray Diffraction	138
6.4 Biaxial Strain–Stress Relationship	143
6.5 Experimental Results	146
6.6 Conclusions	163
References	164

**7 Theory of the Electronic and Optical Properties
of InGaAs/GaAs Quantum Dots**

Oliver Stier	167
7.1 Introduction	167
7.2 General Properties of Confined States in Quantum Dots	168
7.3 Strain in Buried Quantum Dot Structures	170
7.4 Piezoelectric Symmetry Reduction	172
7.5 Confined Single-Particle States	173
7.6 Dipole Transitions Between Zero-Dimensional States	177
7.7 Few-body Effects in the Strong Confinement Regime	180
7.8 Quantum-Confined Stark Effect	193
7.9 Shape Variation Effects	195

7.10 Reliability of State-of-the-Art Calculations	197
7.11 Conclusions	198
References	199

8 Magneto-Tunneling Spectroscopy of Self-Assembled InAs Dots

Laurence Eaves, Amalia Patanè, Peter C. Main	203
8.1 Introduction	203
8.2 Tunneling Diodes Incorporating Self-assembled Quantum Dots ..	204
8.3 Magneto-tunneling Spectroscopy	205
8.4 Prospects and Conclusions	211
References	212

9 Modulation Spectroscopy and Surface Photovoltage Spectroscopy of Semiconductor Quantum Wires and Quantum Dots

Fred H. Pollak	215
9.1 Introduction	215
9.2 Experimental Methods	215
9.3 Lineshape Considerations	219
9.4 Results and Discussion	223
9.5 Summary	237
References	237

10 Optical Properties of Self-Organized Quantum Dots

Robert Heitz	239
10.1 Introduction	239
10.2 Investigated Samples	241
10.3 Excited Exciton Transitions	244
10.4 Exciton-LO-Phonon Coupling.....	250
10.5 Many-Particle States	253
10.6 Exciton Dynamics	257
10.7 Conclusions	266
References	266

11 High Occupancy Effects and Condensation Phenomena in Semiconductor Microcavities and Bulk Semiconductors

Maurice S. Skolnick, Alexander I. Tartakovskii, Raphaël Butté, R. Mark Stevenson, Jeremy J. Baumberg, David M. Whittaker	273
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11.1 Introduction	273
11.2 Experimental Techniques for Microcavity Studies.....	275
11.3 Non-Resonant Excitation	276
11.4 Resonant Excitation	280

11.5 Comparison of Resonant and Non-Resonant Excitation of Microcavities, Polariton Lasers and Optical Parametric Oscillators	285
11.6 Exciton Condensates and Stimulated Scattering in Direct Gap Bulk Materials and Quantum Wells	287
11.7 The Electron-Hole Liquid in Indirect Gap Semiconductors	289
11.8 Summary	294
References	294

Part III Devices**12 Theory of Quantum Dot Lasers**

Marius Grundmann	299
12.1 Introduction	299
12.2 Basic Theory of Quantum Dot Lasers	300
12.3 Carrier Distribution Function	302
12.4 Threshold Current	305
12.5 Characteristic Temperature	307
12.6 Lasing Spectra	308
12.7 High Frequency Modulation	309
12.8 Inter-Sublevel Lasers	314
12.9 Conclusion and Outlook	314
References	315

13 Long-Wavelength InGaAs/GaAs Quantum Dot Lasers

Nikolai N. Ledentsov	317
13.1 Introduction	317
13.2 Quantum Dots	318
13.3 Growth of Long-Wavelength GaAs-Based Quantum Dots	320
13.4 Edge-Emitting Long-Wavelength Quantum Dot Lasers	327
13.5 Degradation Studies	330
13.6 Long-Wavelength Vertical-Cavity Surface-Emitting QD Lasers	331
13.7 Conclusions	334
References	335

14 InP/GaInP Quantum Dot Lasers

Oliver G. Schmidt, Yvonne M. Manz, Karl Eberl	339
14.1 Introduction	339
14.2 Single Layers	339
14.3 Stacked Layers	344
14.4 InP/InGaP Quantum Dot Lasers	347
References	350

15 High Power Quantum Dot Lasers	
Christian Ribbat, Roman Sellin	353
15.1 High Power Laser Diodes	353
15.2 Quantum Dot Lasers	355
15.3 Characteristics of Ridge Wave-Guide Quantum Dot Lasers	357
15.4 Summary	367
References	368
16 Inter-Sublevel Transitions in Quantum Dots and Device Applications	
Alexander Weber	371
16.1 Introduction	371
16.2 Inter-Sublevel Absorption	371
16.3 Inter-Sublevel Emission	377
16.4 Conclusion	387
References	388
17 Progress in Growth and Physics of Nitride-Based Quantum Dots	
Yasuhiko Arakawa	391
17.1 Introduction	391
17.2 Why QDs in GaN-Based Lasers are Important	392
17.3 Electronic States in GaN-Based QDs	394
17.4 Growth and Optical Properties of Self-Assembling InGaN QDs	398
17.5 Growth and Optical Properties of Self-Assembling GaN QDs	401
17.6 Lasing Action of InGaN QD Lasers at Room Temperature	404
17.7 Growth and Optical Properties of Selectively Grown InGaN QDs	406
17.8 Conclusion	408
References	408
18 Ultrafast Optical Properties of Quantum Dot Amplifiers	
Paola Borri	411
18.1 Introduction	411
18.2 Carrier Dynamics in Semiconductor Optical Amplifiers	412
18.3 Heterodyne Pump-Probe Technique	413
18.4 Gain and Refractive Index Dynamics in In(Ga)As QD Amplifiers	416
18.5 Dephasing Time in In(Ga)As QD Amplifiers	423
18.6 Summary	428
References	429
Index	431